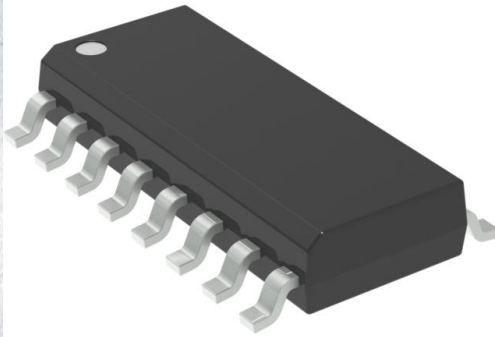


# AU5517DR2 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	AU5517DR2-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	AU5517DR2
Description	IC AMP 2 CURRENT CTRL 16-SOIC
Detailed Description	Transconductance Amplifier 2 Circuit 16-SOIC



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

AU5517DR2

Series:

-

Amplifier Type:

Transconductance

Output Type:

-

Gain Bandwidth Product:

2 MHz

Voltage - Input Offset:

400  $\mu$ V

Current - Output / Channel:

650  $\mu$ A

Voltage - Supply Span (Max):

44 V

Mounting Type:

Surface Mount

Supplier Device Package:

16-SOIC

Manufacturer:

onsemi

Product Status:

Obsolete

Number of Circuits:

2

Slew Rate:

50V/ $\mu$ s

Current - Input Bias:

400 nA

Current - Supply:

2.6mA

Voltage - Supply Span (Min):

44 V

Operating Temperature:

150°C (TJ)

Package / Case:

16-SOIC (0.154", 3.90mm Width)

Base Product Number:

AU5517

## Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8542.33.0001

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



# Dual Operational Transconductance Amplifier

## NE5517

The NE5517 contains two current-controlled transconductance amplifiers, each with a differential input and push-pull output. The NE5517 offers significant design and performance advantages over similar devices for all types of programmable gain applications. Circuit performance is enhanced through the use of linearizing diodes at the inputs which enable a 10 dB signal-to-noise improvement referenced to 0.5% THD. The NE5517 is suited for a wide variety of industrial and consumer applications.

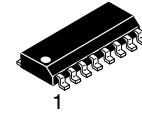
Constant impedance of the buffers on the chip allow general use of the NE5517. These buffers are made of Darlington transistors and a biasing network that virtually eliminate the change of offset voltage due to a burst in the bias current  $I_{ABC}$ , hence eliminating the audible noise that could otherwise be heard in high quality audio applications.

### Features

- Constant Impedance Buffers
- $\Delta V_{BE}$  of Buffer is Constant with Amplifier  $I_{BIAS}$  Change
- Excellent Matching Between Amplifiers
- Linearizing Diodes
- High Output Signal-to-Noise Ratio
- This is a Pb-Free Device

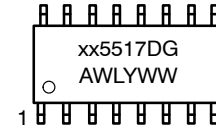
### Applications

- Multiplexers
- Timers
- Electronic Music Synthesizers
- Dolby® HX Systems
- Current-Controlled Amplifiers, Filters
- Current-Controlled Oscillators, Impedances



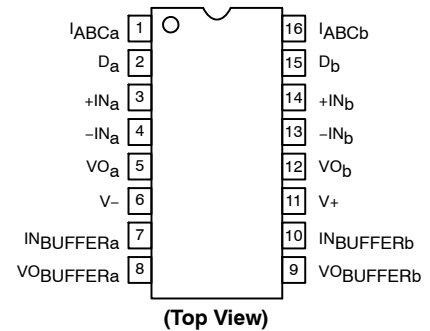
SOIC-16  
D SUFFIX  
CASE 751B

### MARKING DIAGRAM



xx = NE  
A = Assembly Location  
WL = Wafer Lot  
YY, Y = Year  
WW = Work Week  
G = Pb-Free Package

### PIN CONNECTIONS



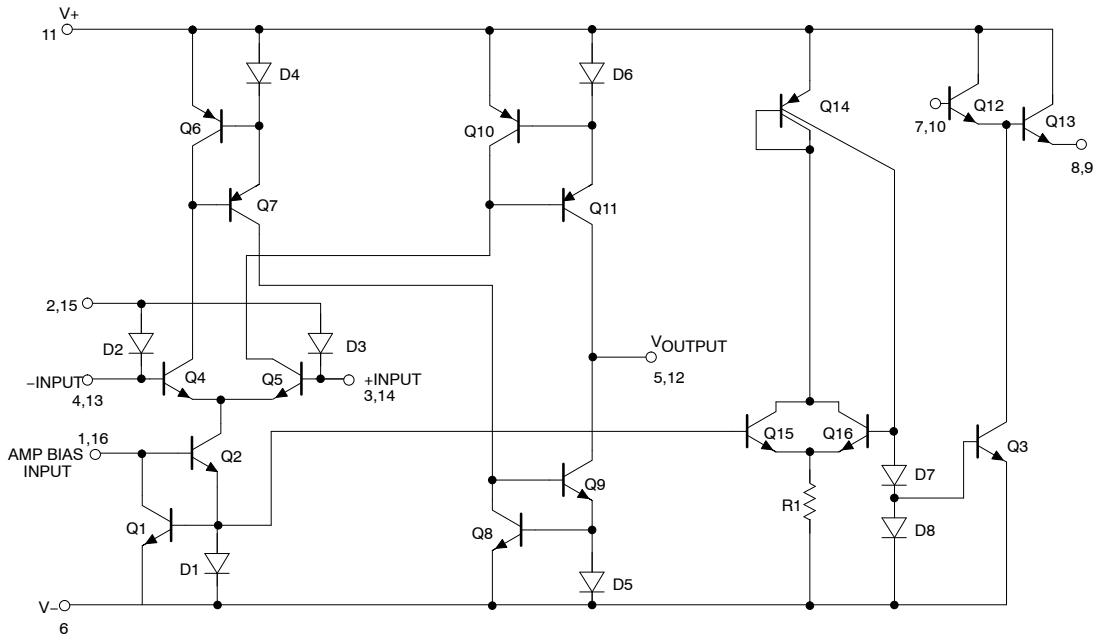
### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

**NE5517**

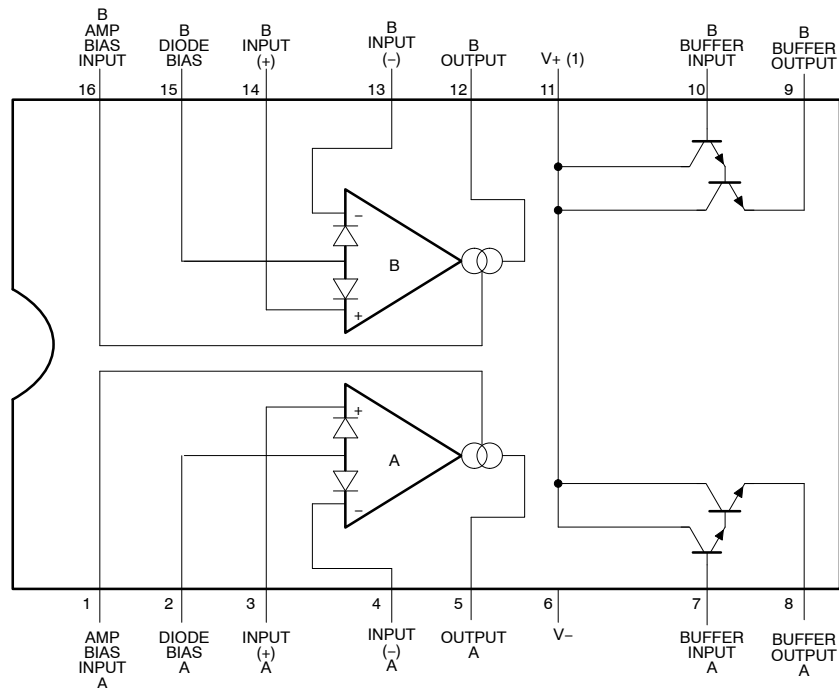
**PIN DESCRIPTION**

Pin No.	Symbol	Description
1	$I_{ABCa}$	Amplifier Bias Input A
2	$D_a$	Diode Bias A
3	$+IN_a$	Non-inverted Input A
4	$-IN_a$	Inverted Input A
5	$VO_a$	Output A
6	$V-$	Negative Supply
7	$IN_{BUFFERa}$	Buffer Input A
8	$VO_{BUFFERa}$	Buffer Output A
9	$VO_{BUFFERb}$	Buffer Output B
10	$IN_{BUFFERb}$	Buffer Input B
11	$V+$	Positive Supply
12	$VO_b$	Output B
13	$-IN_b$	Inverted Input B
14	$+IN_b$	Non-inverted Input B
15	$D_b$	Diode Bias B
16	$I_{ABCb}$	Amplifier Bias Input B



**Figure 1. Circuit Schematic**

**NE5517**



NOTE: V<sub>+</sub> of output buffers and amplifiers are internally connected.

**Figure 2. Connection Diagram**

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Supply Voltage (Note 1)	V <sub>S</sub>	44 V <sub>DC</sub> or ±22	V
Power Dissipation, T <sub>amb</sub> = 25 °C (Still Air) (Note 2)	P <sub>D</sub>	1125	mW
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	140	°C/W
Differential Input Voltage	V <sub>IN</sub>	±5.0	V
Diode Bias Current	I <sub>D</sub>	2.0	mA
Amplifier Bias Current	I <sub>ABC</sub>	2.0	mA
Output Short-Circuit Duration	I <sub>SC</sub>	Indefinite	
Buffer Output Current (Note 3)	I <sub>OUT</sub>	20	mA
Operating Temperature Range	T <sub>amb</sub>	0 °C to +70 °C	°C
Operating Junction Temperature	T <sub>J</sub>	150	°C
DC Input Voltage	V <sub>DC</sub>	+V <sub>S</sub> to -V <sub>S</sub>	
Storage Temperature Range	T <sub>stg</sub>	-65 °C to +150 °C	°C
Lead Soldering Temperature (10 sec max)	T <sub>slid</sub>	230	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. For selections to a supply voltage above ±22 V, contact factory.
2. The following derating factors should be applied above 25 °C  
D package at 7.1 mW/°C.
3. Buffer output current should be limited so as to not exceed package dissipation.

## NE5517

## ELECTRICAL CHARACTERISTICS (Note 4)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
Input Offset Voltage	Overtemperature Range $I_{ABC} = 5.0 \mu A$	$V_{OS}$		0.4 0.3	5.0 5.0	mV
$\Delta V_{OS}/\Delta T$	Avg. TC of Input Offset Voltage			7.0		$\mu V/^{\circ}C$
$V_{OS}$ Including Diodes	Diode Bias Current ( $I_D$ ) = 500 $\mu A$			0.5	5	mV
Input Offset Change	$5.0 \mu A \leq I_{ABC} \leq 500 \mu A$	$V_{OS}$		0.1		mV
Input Offset Current		$I_{OS}$		0.1	0.6	$\mu A$
$\Delta I_{OS}/\Delta T$	Avg. TC of Input Offset Current			0.001		$\mu A/^{\circ}C$
Input Bias Current	Overtemperature Range	$I_{BIAS}$		0.4 1.0	5.0 8.0	$\mu A$
$\Delta I_B/\Delta T$	Avg. TC of Input Current			0.01		$\mu A/^{\circ}C$
Forward Transconductance	Overtemperature Range	$g_M$	6700 5400	9600	13000	$\mu mho$
$g_M$ Tracking				0.3		dB
Peak Output Current	$R_L = 0, I_{ABC} = 5.0 \mu A$ $R_L = 0, I_{ABC} = 500 \mu A$ $R_L = 0, \text{Overtemperature Range}$	$I_{OUT}$	350 300	5.0 500	650	$\mu A$
Peak Output Voltage Positive Negative	$R_L = \infty, 5.0 \mu A \leq I_{ABC} \leq 500 \mu A$ $R_L = \infty, 5.0 \mu A \leq I_{ABC} \leq 500 \mu A$	$V_{OUT}$	+12 -12	+14.2 -14.4		V
Supply Current	$I_{ABC} = 500 \mu A$ , both channels	$I_{CC}$		2.6	4.0	mA
$V_{OS}$ Sensitivity Positive Negative	$\Delta V_{OS}/\Delta V_+$ $\Delta V_{OS}/\Delta V_-$			20 20	150 150	$\mu V/V$
Common-mode Rejection Ratio		CMRR	80	110		dB
Common-mode Range			$\pm 12$	$\pm 13.5$		V
Crosstalk	Referred to Input (Note 5) 20 Hz < f < 20 kHz			100		dB
Differential Input Current	$I_{ABC} = 0$ , Input = $\pm 4.0$ V	$I_{IN}$		0.02	100	nA
Leakage Current	$I_{ABC} = 0$ (Refer to Test Circuit)			0.2	100	nA
Input Resistance		$R_{IN}$	10	26		k $\Omega$
Open-loop Bandwidth		$B_W$		2.0		MHz
Slew Rate	Unity Gain Compensated	SR		50		V/ $\mu s$
Buffer Input Current	5	$I_{NBUFFER}$		0.4	5.0	$\mu A$
Peak Buffer Output Voltage	5	$V_{OBUFFER}$	10			V
$\Delta V_{BE}$ of Buffer	Refer to Buffer $V_{BE}$ Test Circuit (Note 6)			0.5	5.0	mV

4. These specifications apply for  $V_S = \pm 15$  V,  $T_{amb} = 25^{\circ}C$ , amplifier bias current ( $I_{ABC}$ ) = 500  $\mu A$ , Pins 2 and 15 open unless otherwise specified. The inputs to the buffers are grounded and outputs are open.

5. These specifications apply for  $V_S = \pm 15$  V,  $I_{ABC} = 500 \mu A$ ,  $R_{OUT} = 5.0$  k $\Omega$  connected from the buffer output to  $-V_S$  and the input of the buffer is connected to the transconductance amplifier output.

6.  $V_S = \pm 15$ ,  $R_{OUT} = 5.0$  k $\Omega$  connected from Buffer output to  $-V_S$  and  $5.0 \mu A \leq I_{ABC} \leq 500 \mu A$ .

# NE5517

## TYPICAL PERFORMANCE CHARACTERISTICS

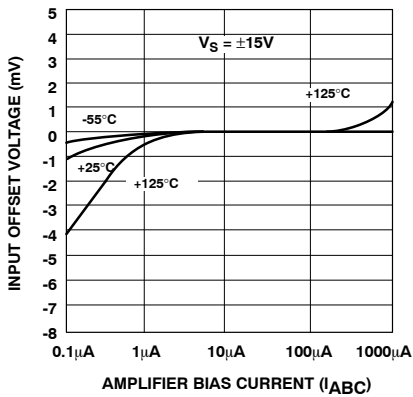


Figure 3. Input Offset Voltage

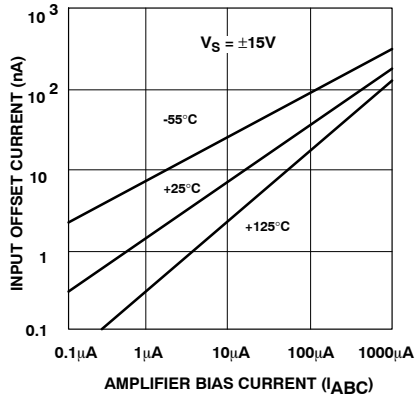


Figure 4. Input Bias Current

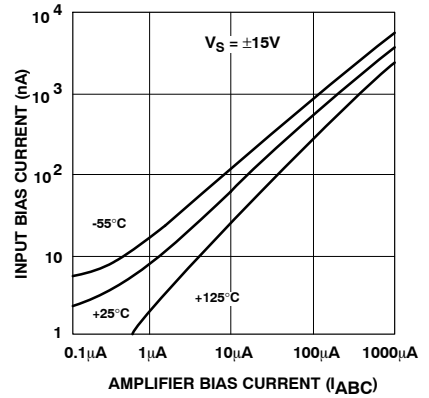


Figure 5. Input Bias Current

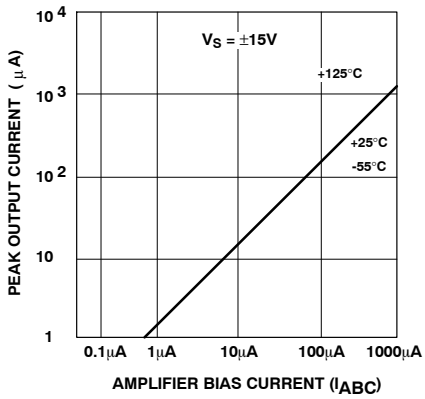


Figure 6. Peak Output Current

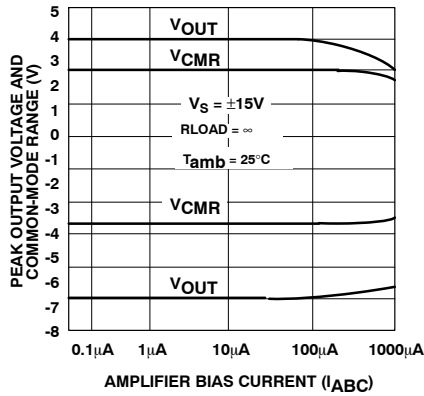


Figure 7. Peak Output Voltage and Common-Mode Range

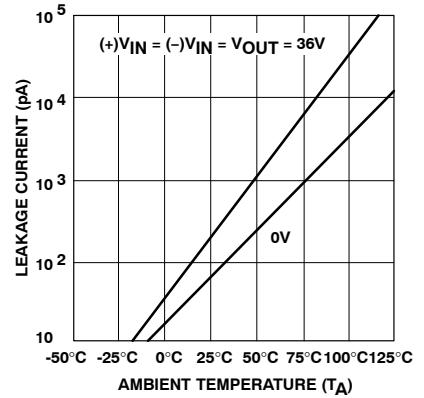


Figure 8. Leakage Current

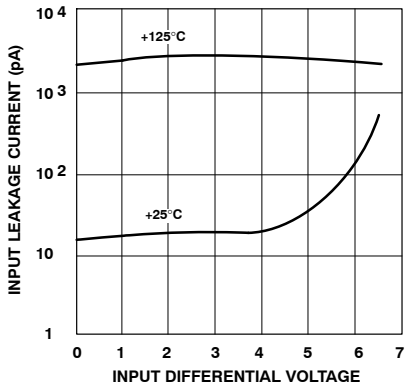


Figure 9. Input Leakage

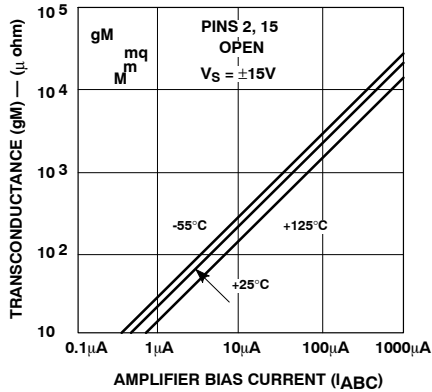


Figure 10. Transconductance

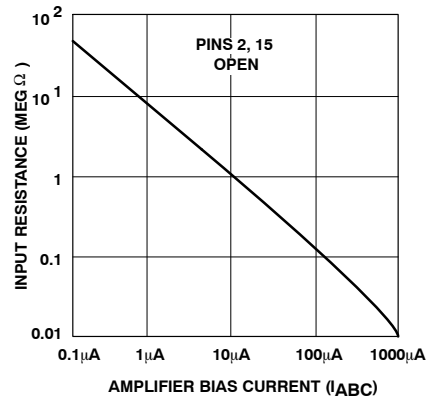


Figure 11. Input Resistance

# NE5517

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

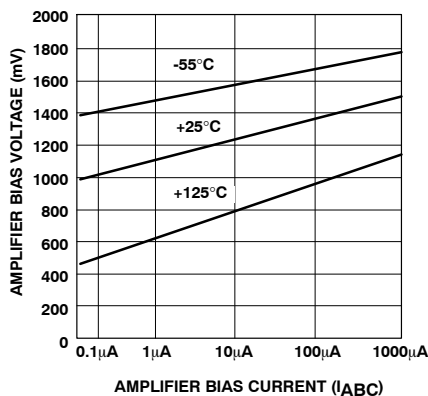


Figure 12. Amplifier Bias Voltage vs. Amplifier Bias Current

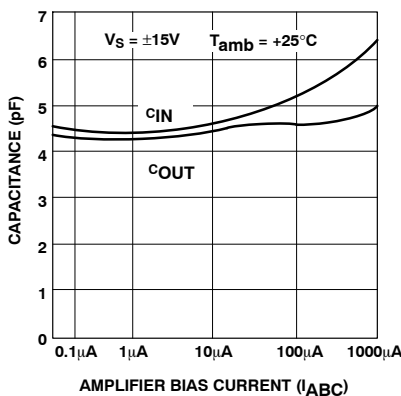


Figure 13. Input and Output Capacitance

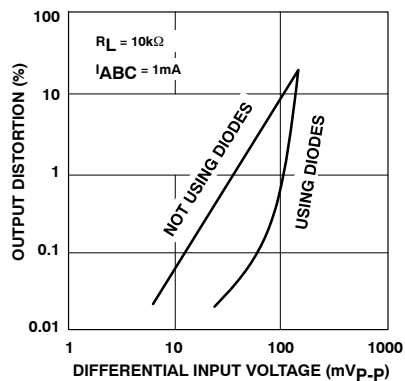


Figure 14. Distortion vs. Differential Input Voltage

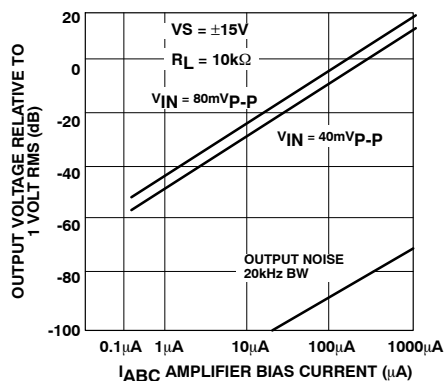


Figure 15. Voltage vs. Amplifier Bias Current

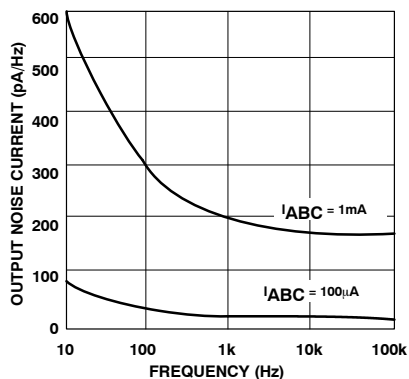


Figure 16. Noise vs. Frequency

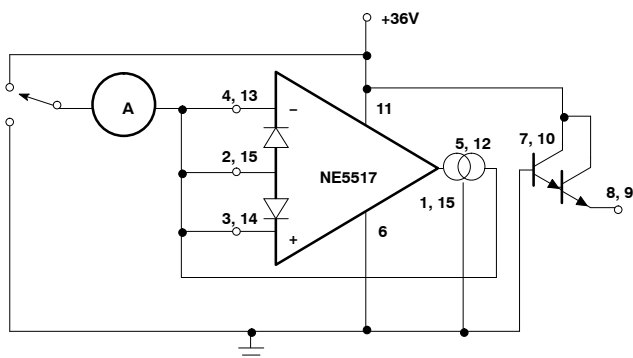


Figure 17. Leakage Current Test Circuit

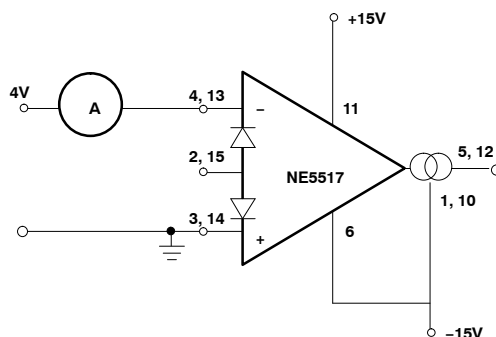


Figure 18. Differential Input Current Test Circuit

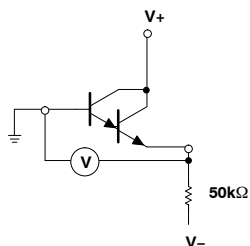


Figure 19. Buffer  $V_{BE}$  Test Circuit



# NE5517

## APPLICATIONS

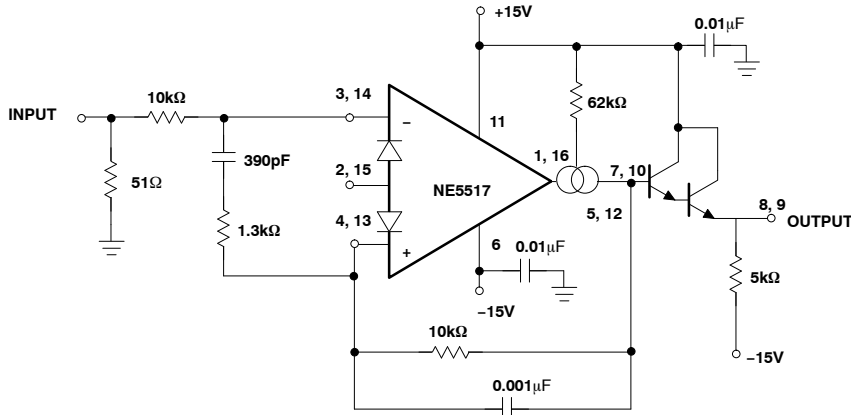


Figure 20. Unity Gain Follower

### CIRCUIT DESCRIPTION

The circuit schematic diagram of one-half of the NE5517, a dual operational transconductance amplifier with linearizing diodes and impedance buffers, is shown in Figure 21.

#### Transconductance Amplifier

The transistor pair, Q<sub>4</sub> and Q<sub>5</sub>, forms a transconductance stage. The ratio of their collector currents (I<sub>4</sub> and I<sub>5</sub>, respectively) is defined by the differential input voltage, V<sub>IN</sub>, which is shown in Equation 1.

$$V_{IN} = \frac{KT}{q} \ln \frac{I_5}{I_4} \quad (\text{eq. 1})$$

Where V<sub>IN</sub> is the difference of the two input voltages

KT ≅ 26 mV at room temperature (300°k).

Transistors Q<sub>1</sub>, Q<sub>2</sub> and diode D<sub>1</sub> form a current mirror which focuses the sum of current I<sub>4</sub> and I<sub>5</sub> to be equal to amplifier bias current I<sub>B</sub>:

$$I_4 + I_5 = I_B \quad (\text{eq. 2})$$

If V<sub>IN</sub> is small, the ratio of I<sub>5</sub> and I<sub>4</sub> will approach unity and the Taylor series of ln function can be approximated as

$$\frac{KT}{q} \ln \frac{I_5}{I_4} \approx \frac{KT}{q} \frac{I_5 - I_4}{I_4} \quad (\text{eq. 3})$$

$$\text{and } I_4 \cong I_5 \cong I_B$$

$$\frac{KT}{q} \ln \frac{I_5}{I_4} \approx \frac{KT}{q} \frac{I_5 - I_4}{1/2 I_B} = \frac{2KT}{q} \frac{I_5 - I_4}{I_B} = V_{IN} \quad (\text{eq. 4})$$

$$I_5 - I_4 = V_{IN} \frac{(I_B^q)}{2KT}$$

The remaining transistors (Q<sub>6</sub> to Q<sub>11</sub>) and diodes (D<sub>4</sub> to D<sub>6</sub>) form three current mirrors that produce an output current equal to I<sub>5</sub> minus I<sub>4</sub>. Thus:

$$V_{IN} \left( \frac{I_B^q}{2KT} \right) = I_O \quad (\text{eq. 5})$$

The term  $\frac{(I_B^q)}{2KT}$  is then the transconductance of the amplifier and is proportional to I<sub>B</sub>.

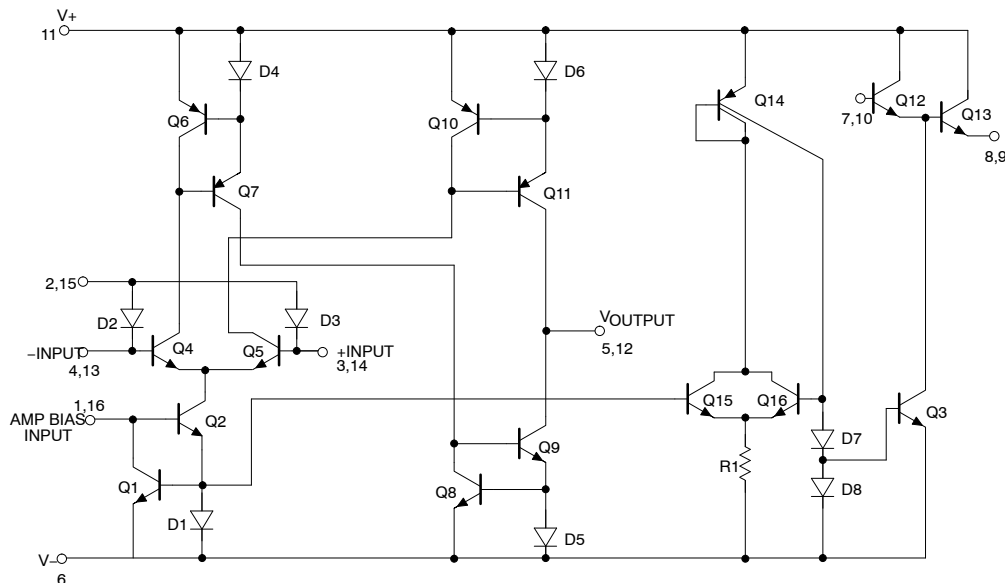


Figure 21. Circuit Diagram of NE5517

## NE5517

### Linearizing Diodes

For  $V_{IN}$  greater than a few millivolts, Equation 3 becomes invalid and the transconductance increases non-linearly. Figure 22 shows how the internal diodes can linearize the transfer function of the operational amplifier. Assume  $D_2$  and  $D_3$  are biased with current sources and the input signal current is  $I_S$ . Since  $I_4 + I_5 = I_B$  and  $I_5 - I_4 = I_O$ , that is:  $I_4 = (I_B - I_O)$ ,  $I_5 = (I_B + I_O)$

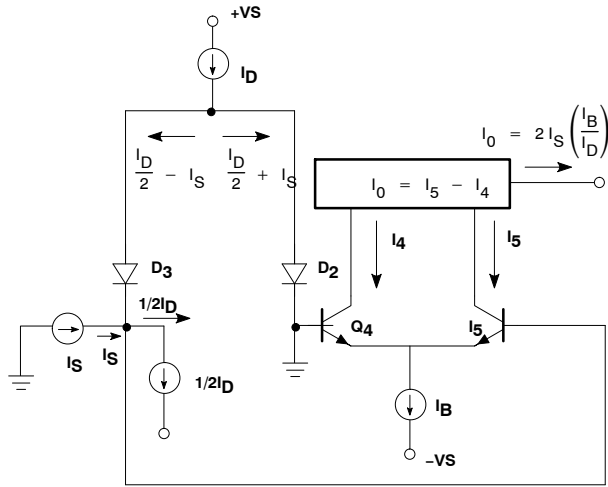


Figure 22. Linearizing Diode

For the diodes and the input transistors that have identical geometries and are subject to similar voltages and temperatures, the following equation is true:

$$\frac{T}{q} \ln \frac{I_D/2 + I_S}{I_D/2 - I_S} = \frac{KT}{q} \ln \frac{1/2(I_B + I_O)}{1/2(I_B - I_O)} \quad (\text{eq. 6})$$

$$I_O = I_S \frac{2I_B}{I_D} \text{ for } |I_S| < \frac{I_D}{2}$$

The only limitation is that the signal current should not exceed  $I_D$ .

### Impedance Buffer

The upper limit of transconductance is defined by the maximum value of  $I_B$  (2.0 mA). The lowest value of  $I_B$  for which the amplifier will function therefore determines the overall dynamic range. At low values of  $I_B$ , a buffer with very low input bias current is desired. A Darlington amplifier with constant-current source ( $Q_{14}$ ,  $Q_{15}$ ,  $Q_{16}$ ,  $D_7$ ,  $D_8$ , and  $R_1$ ) suits the need.

## APPLICATIONS

### Voltage-Controlled Amplifier

In Figure 23, the voltage divider  $R_2$ ,  $R_3$  divides the input-voltage into small values (mV range) so the amplifier operates in a linear manner.

It is:

$$I_{OUT} = -V_{IN} \cdot \frac{R_3}{R_2 + R_3} \cdot g_M$$

$$V_{OUT} = I_{OUT} \cdot R_L$$

$$A = \frac{V_{OUT}}{V_{IN}} = \frac{R_3}{R_2 + R_3} \cdot g_M \cdot R_L$$

$$(3) \quad g_M = 19.2 I_{ABC}$$

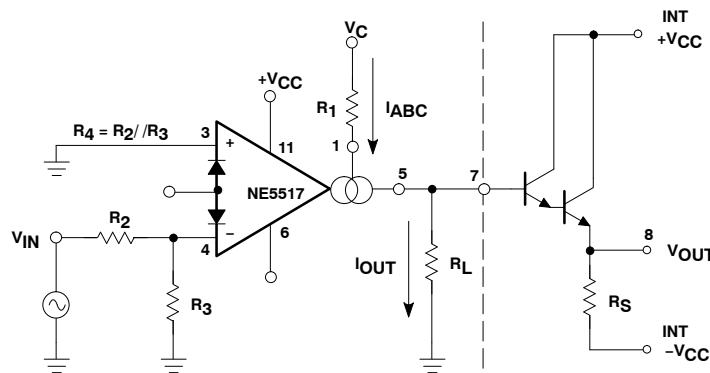
$$(g_M \text{ in } \mu\text{mhos for } I_{ABC} \text{ in mA})$$

Since  $g_M$  is directly proportional to  $I_{ABC}$ , the amplification is controlled by the voltage  $V_C$  in a simple way.

When  $V_C$  is taken relative to  $-V_{CC}$  the following formula is valid:

$$I_{ABC} = \frac{(V_C - 1.2V)}{R_1}$$

The 1.2 V is the voltage across two base-emitter baths in the current mirrors. This circuit is the base for many applications of the NE5517.



TYPICAL VALUES:  $R_1 = 47k\Omega$   
 $R_2 = 10k\Omega$   
 $R_3 = 200\Omega$   
 $R_4 = 200\Omega$   
 $R_L = 100k\Omega$   
 $R_S = 47k\Omega$

Figure 23.

## NE5517

### Stereo Amplifier With Gain Control

Figure 24 shows a stereo amplifier with variable gain via a control input. Excellent tracking of typical 0.3 dB is easy to achieve. With the potentiometer,  $R_P$ , the offset can be adjusted. For AC-coupled amplifiers, the potentiometer may be replaced with two 510  $\Omega$  resistors.

### Modulators

Because the transconductance of an OTA (Operational Transconductance Amplifier) is directly proportional to  $I_{ABC}$ , the amplification of a signal can be controlled easily. The output current is the product from transconductance  $\times$  input voltage. The circuit is effective up to approximately 200 kHz. Modulation of 99% is easy to achieve.

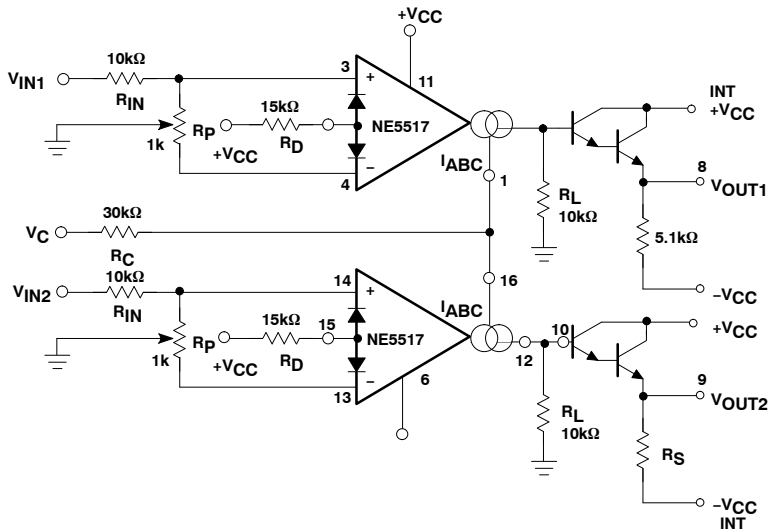


Figure 24. Gain-Controlled Stereo Amplifier

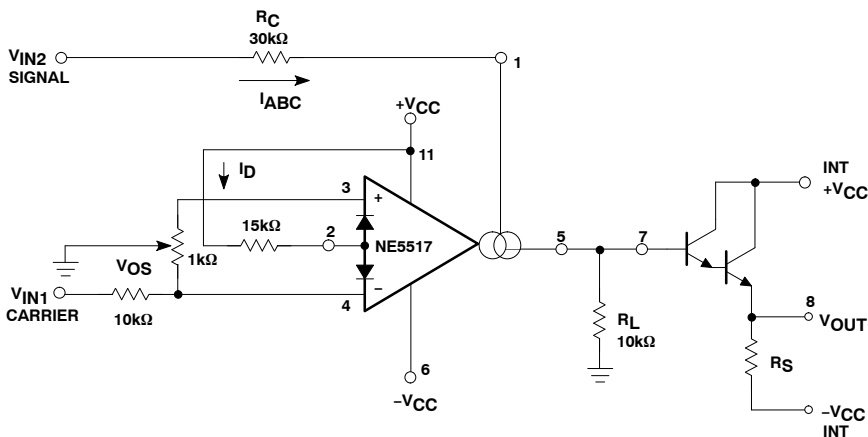


Figure 25. Amplitude Modulator

## NE5517

### Voltage-Controlled Resistor (VCR)

Because an OTA is capable of producing an output current proportional to the input voltage, a voltage variable resistor can be made. Figure 26 shows how this is done. A voltage presented at the  $R_X$  terminals forces a voltage at the input. This voltage is multiplied by  $g_M$  and thereby forces a current through the  $R_X$  terminals:

$$R_x = \frac{R + R_A}{g_M + R_A}$$

where  $g_M$  is approximately 19.21  $\mu$ MHOs at room temperature. Figure 27 shows a Voltage Controlled Resistor using linearizing diodes. This improves the noise performance of the resistor.

### Voltage-Controlled Filters

Figure 28 shows a Voltage Controlled Low-Pass Filter. The circuit is a unity gain buffer until  $X_C/g_M$  is equal to  $R/R_A$ . Then, the frequency response rolls off at a 6dB per octave with the -3 dB point being defined by the given equations. Operating in the same manner, a Voltage Controlled High-Pass Filter is shown in Figure 29. Higher order filters can be made using additional amplifiers as shown in Figures 30 and 31.

### Voltage-Controlled Oscillators

Figure 32 shows a voltage-controlled triangle-square wave generator. With the indicated values a range from 2.0 Hz to 200 kHz is possible by varying  $I_{ABC}$  from 1.0 mA to 10  $\mu$ A.

The output amplitude is determined by  $I_{OUT} \times R_{OUT}$ .

Please notice the differential input voltage is not allowed to be above 5.0 V.

With a slight modification of this circuit you can get the sawtooth pulse generator, as shown in Figure 33.

### APPLICATION HINTS

To hold the transconductance  $g_M$  within the linear range,  $I_{ABC}$  should be chosen not greater than 1.0 mA. The current mirror ratio should be as accurate as possible over the entire current range. A current mirror with only two transistors is not recommended. A suitable current mirror can be built with a PNP transistor array which causes excellent matching and thermal coupling among the transistors. The output current range of the DAC normally reaches from 0 to -2.0 mA. In this application, however, the current range is set through  $R_{REF}$  (10 k $\Omega$ ) to 0 to -1.0 mA.

$$I_{DACMAX} = 2 \cdot \frac{V_{REF}}{R_{REF}} = 2 \cdot \frac{5V}{10k\Omega} = 1mA$$

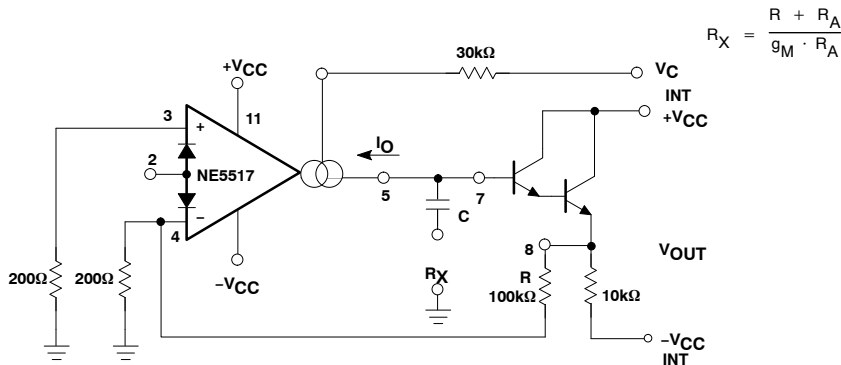


Figure 26. VCR

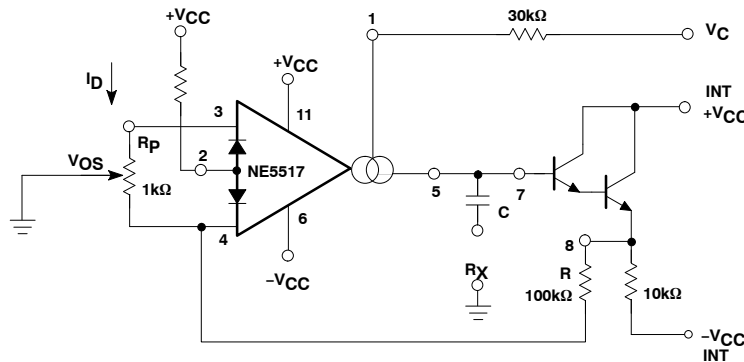
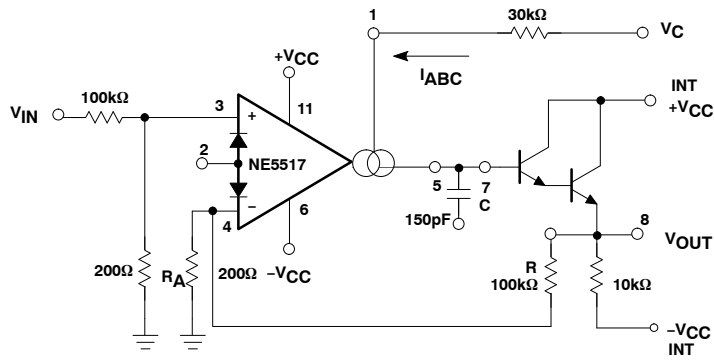


Figure 27. VCR with Linearizing Diodes

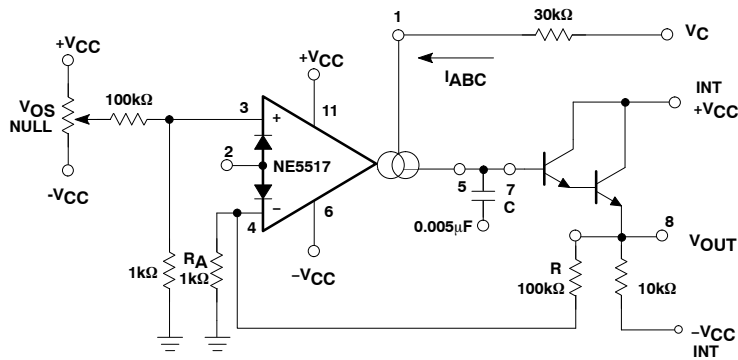
### NE5517



NOTE:

$$f_O = \frac{R_A g_M}{g(R + R_A) 2\pi C}$$

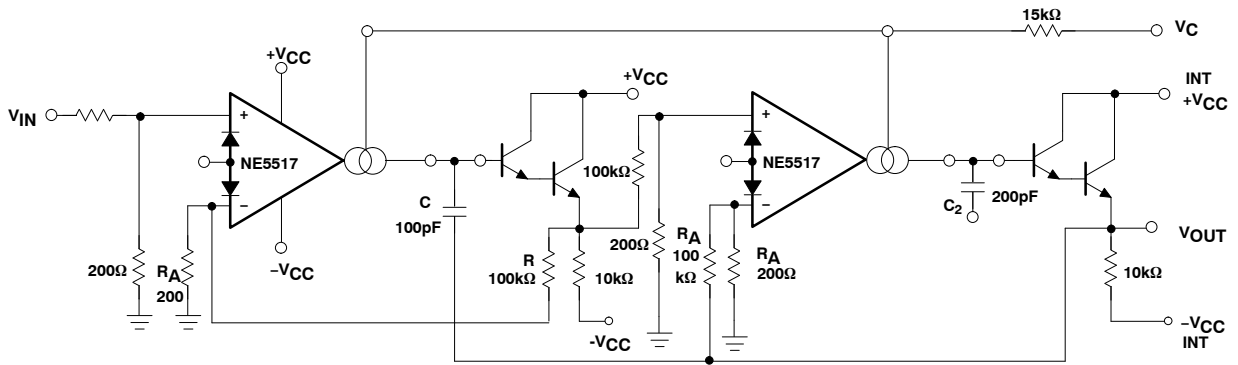
Figure 28. Voltage-Controlled Low-Pass Filter



NOTE:

$$f_O = \frac{R_A g_M}{g(R + R_A) 2\pi C}$$

Figure 29. Voltage-Controlled High-Pass Filter



NOTE:

$$f_O = \frac{R_A g_M}{(R + R_A) 2\pi C}$$

Figure 30. Butterworth Filter - 2nd Order



### NE5517

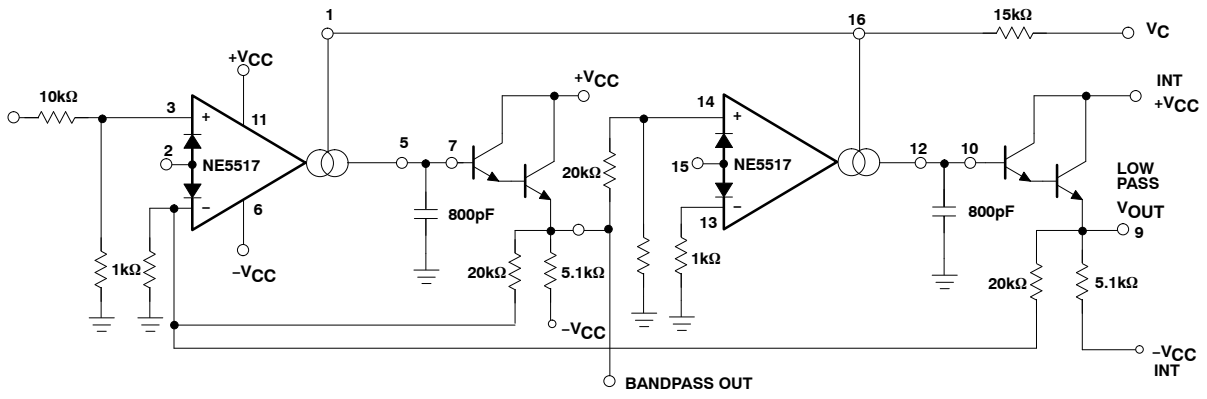


Figure 31. State Variable Filter

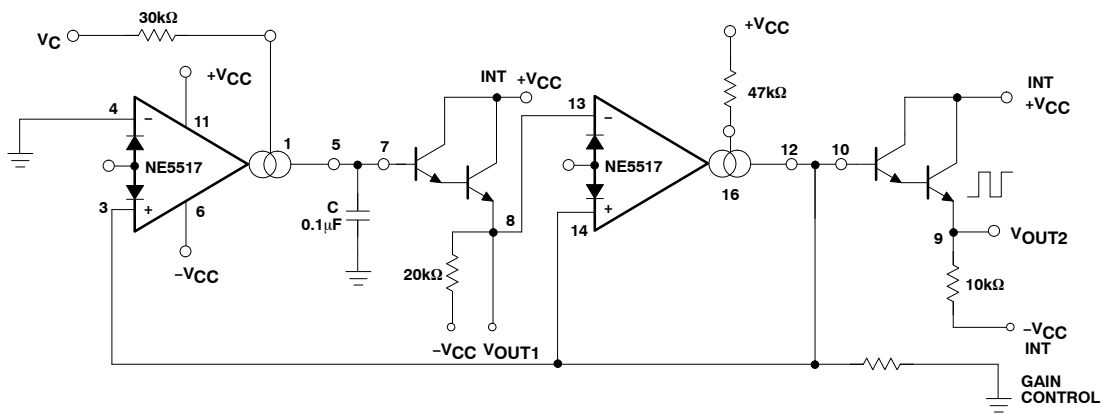


Figure 32. Triangle-Square Wave Generator (VCO)

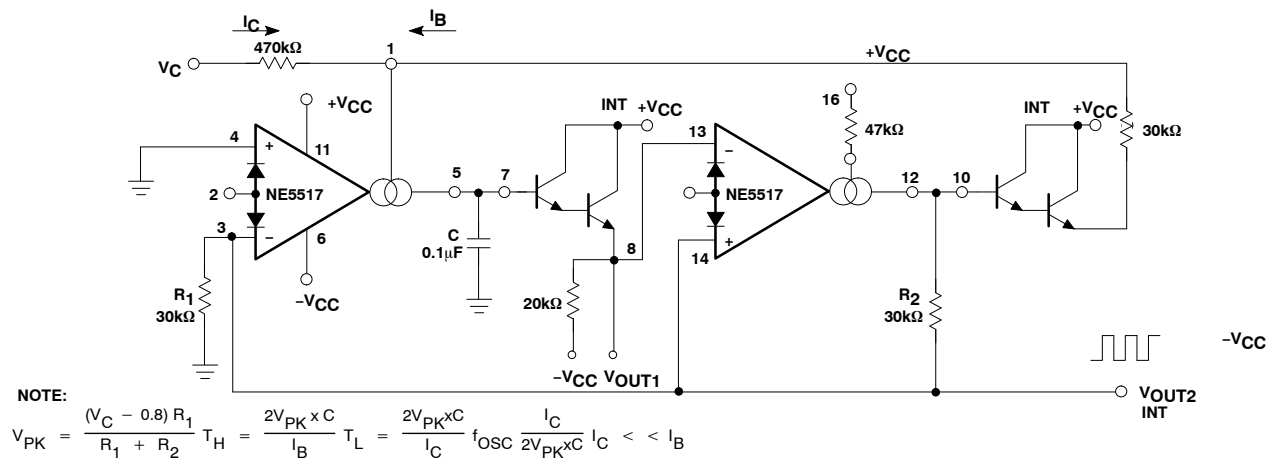


Figure 33. Sawtooth Pulse VCO

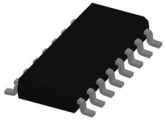
**NE5517****ORDERING INFORMATION**

<b>Device</b>	<b>Temperature Range</b>	<b>Package</b>	<b>Shipping†</b>
NE5517DR2G	0 to +70 °C	SOIC-16 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**

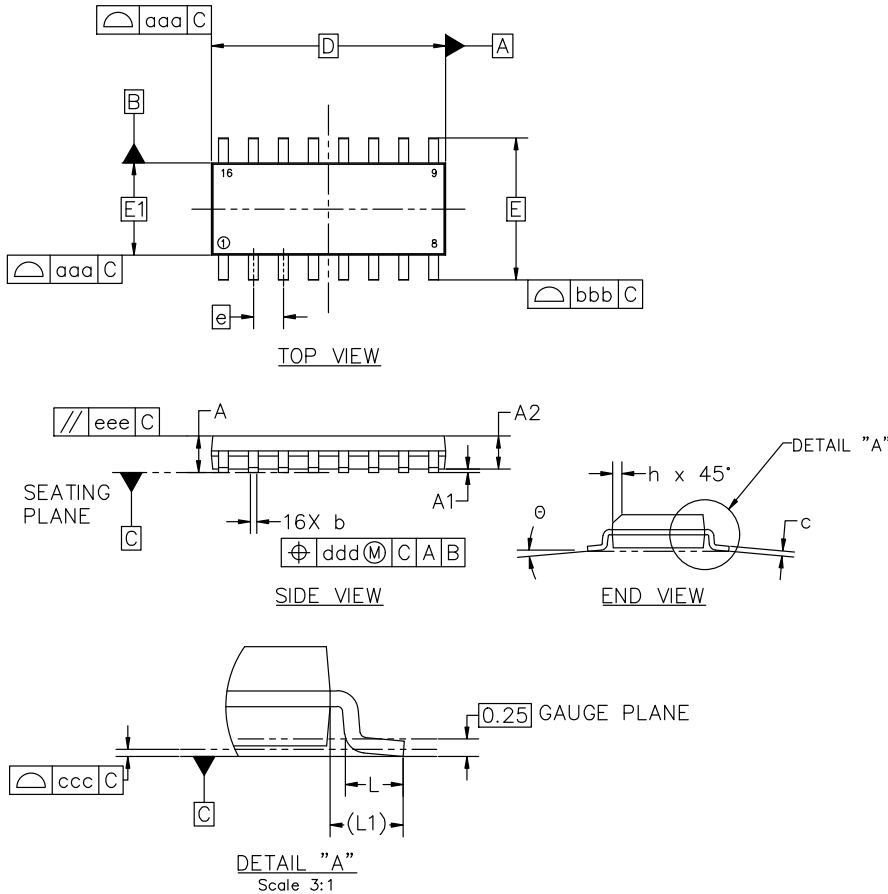


**SOIC-16 9.90x3.90x1.37 1.27P  
CASE 751B  
ISSUE M**

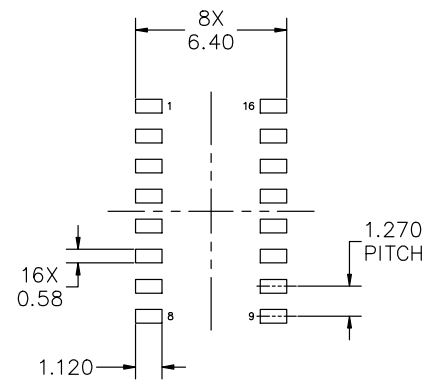
DATE 18 OCT 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D

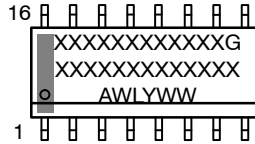
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<b>DESCRIPTION:</b>	<b>SOIC-16 9.90X3.90X1.37 1.27P</b>	<b>PAGE 1 OF 2</b>

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**SOIC-16 9.90x3.90x1.37 1.27P**  
**CASE 751B**  
**ISSUE M**

DATE 18 OCT 2024

**GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code  
 A = Assembly Location  
 WL = Wafer Lot  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

<p><b>STYLE 1:</b></p> <p>PIN 1. COLLECTOR                  2. BASE                  3. EMITTER                  4. NO CONNECTION                  5. EMITTER                  6. BASE                  7. COLLECTOR                  8. COLLECTOR                  9. BASE                  10. EMITTER                  11. NO CONNECTION                  12. EMITTER                  13. BASE                  14. COLLECTOR                  15. EMITTER                  16. COLLECTOR</p>	<p><b>STYLE 2:</b></p> <p>PIN 1. CATHODE                  2. ANODE                  3. NO CONNECTION                  4. CATHODE                  5. CATHODE                  6. NO CONNECTION                  7. ANODE                  8. CATHODE                  9. CATHODE                  10. ANODE                  11. NO CONNECTION                  12. CATHODE                  13. CATHODE                  14. NO CONNECTION                  15. ANODE                  16. CATHODE</p>	<p><b>STYLE 3:</b></p> <p>PIN 1. COLLECTOR, DYE #1                  2. BASE, #1                  3. EMITTER, #1                  4. COLLECTOR, #1                  5. COLLECTOR, #2                  6. BASE, #2                  7. EMITTER, #2                  8. COLLECTOR, #2                  9. COLLECTOR, #3                  10. BASE, #3                  11. EMITTER, #3                  12. COLLECTOR, #3                  13. COLLECTOR, #4                  14. BASE, #4                  15. EMITTER, #4                  16. COLLECTOR, #4</p>	<p><b>STYLE 4:</b></p> <p>PIN 1. COLLECTOR, DYE #1                  2. COLLECTOR, #1                  3. COLLECTOR, #2                  4. COLLECTOR, #2                  5. COLLECTOR, #3                  6. COLLECTOR, #3                  7. COLLECTOR, #4                  8. COLLECTOR, #4                  9. BASE, #4                  10. EMITTER, #4                  11. BASE, #3                  12. EMITTER, #3                  13. BASE, #2                  14. EMITTER, #2                  15. BASE, #1                  16. EMITTER, #1</p>
<p><b>STYLE 5:</b></p> <p>PIN 1. DRAIN, DYE #1                  2. DRAIN, #1                  3. DRAIN, #2                  4. DRAIN, #2                  5. DRAIN, #3                  6. DRAIN, #3                  7. DRAIN, #4                  8. DRAIN, #4                  9. GATE, #4                  10. SOURCE, #4                  11. GATE, #3                  12. SOURCE, #3                  13. GATE, #2                  14. SOURCE, #2                  15. GATE, #1                  16. SOURCE, #1</p>	<p><b>STYLE 6:</b></p> <p>PIN 1. CATHODE                  2. CATHODE                  3. CATHODE                  4. CATHODE                  5. CATHODE                  6. CATHODE                  7. CATHODE                  8. CATHODE                  9. ANODE                  10. ANODE                  11. ANODE                  12. ANODE                  13. ANODE                  14. ANODE                  15. ANODE                  16. ANODE</p>	<p><b>STYLE 7:</b></p> <p>PIN 1. SOURCE N-CH                  2. COMMON DRAIN (OUTPUT)                  3. COMMON DRAIN (OUTPUT)                  4. GATE P-CH                  5. COMMON DRAIN (OUTPUT)                  6. COMMON DRAIN (OUTPUT)                  7. COMMON DRAIN (OUTPUT)                  8. SOURCE P-CH                  9. SOURCE P-CH                  10. COMMON DRAIN (OUTPUT)                  11. COMMON DRAIN (OUTPUT)                  12. COMMON DRAIN (OUTPUT)                  13. GATE N-CH                  14. COMMON DRAIN (OUTPUT)                  15. COMMON DRAIN (OUTPUT)                  16. SOURCE N-CH</p>	

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